



UV-B Sensor GUVB-S11SD

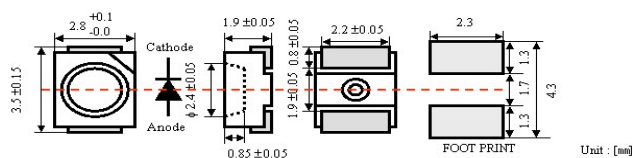


- Features**
- Aluminium Gallium Nitride Based Material
 - Schottky-type Photodiode
 - Photovoltaic Mode Operation
 - Good Visible Blindness
 - High Responsivity & Low Dark Current



- Applications**
- UV Index Monitoring

Outline Diagrams and Dimensions



Absolute Maximum Ratings

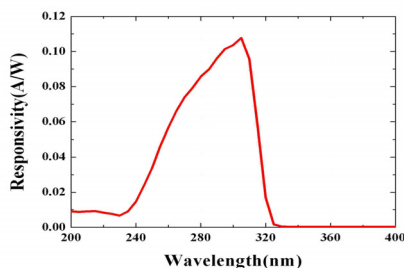
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	°C	
Operating Temperature	T_{op}	-30	85	°C	
Reverse Voltage	$V_{r, max.}$		3	V	
Forward Current	$I_{f, max.}$		1	mA	
Optical Source Power Range	P_{opt}	0.1	100,000	$\mu W/cm^2$	UVB Lamp
Soldering Temperature	T_{sol}		260	°C	within 10 sec.

*Notice: apply to us in the case that Optical Source Power is over $100,000 \mu W/cm^2$.

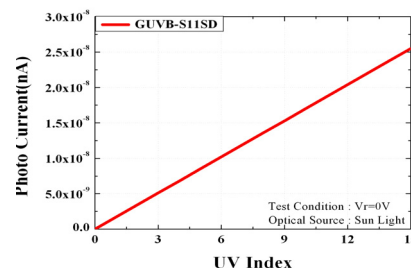
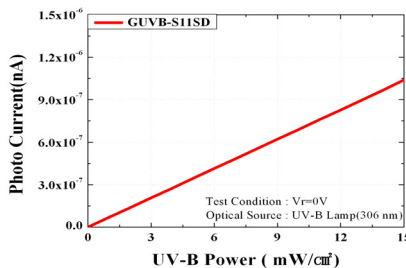
Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			1	nA	$V_r = 0.1 V$
Photo Current	I_{ph}		69		nA	UVB Lamp, $1 mW/cm^2$
			1.4		nA	1 UVI
Temperature Coefficient	I_{tc}		0.1		%/°C	UVB Lamp
Responsivity	R		0.11		A/W	$\lambda = 300 nm, V_r = 0 V$
Spectral Detection Range	λ	240		320	nm	10% of R
Active area			0.076		mm ²	

Responsivity Curve



Photocurrent along UV Power



Caution

ESD can damage the device hence please avoid ESD.